

# ABSTRACT

A semiconductor system having a pn transition and a method for manufacturing a semiconductor system are disclosed. The semiconductor system is designed in the form of a chip having an edge region, the semiconductor system includes a first layer of a first conductivity type and a second layer of a second conductivity type, which is of opposite polarity to the first conductivity type. The first layer has an edge region and a center region, the pn transition being provided between the first layer and the second layer. The second layer is more weakly doped in its edge region than in its center region, and the boundary surface of the pn transition at the edge region is non-parallel to the main chip plane.